

ABSTRACT

An integrated circuit device may include a fin-type active region extending in a first direction on a substrate; an insulating separation structure extending in a second direction that intersects the first direction on the fin-type active region; a pair of split gate lines spaced apart from each other with the insulating separation structure therebetween and extending in the second direction to be aligned with the insulating separation structure; a pair of source/drain regions located on the fin-type active region and spaced apart from each other with the insulating separation structure therebetween; and a jumper contact located over the insulating separation structure and connected between the pair of source/drain regions.

FIG. 2A